

Device Modeling Report

COMPONENTS:
DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD
PART NUMBER: 1SR139-400
MANUFACTURER: ROHM
REMARK: TC=150C

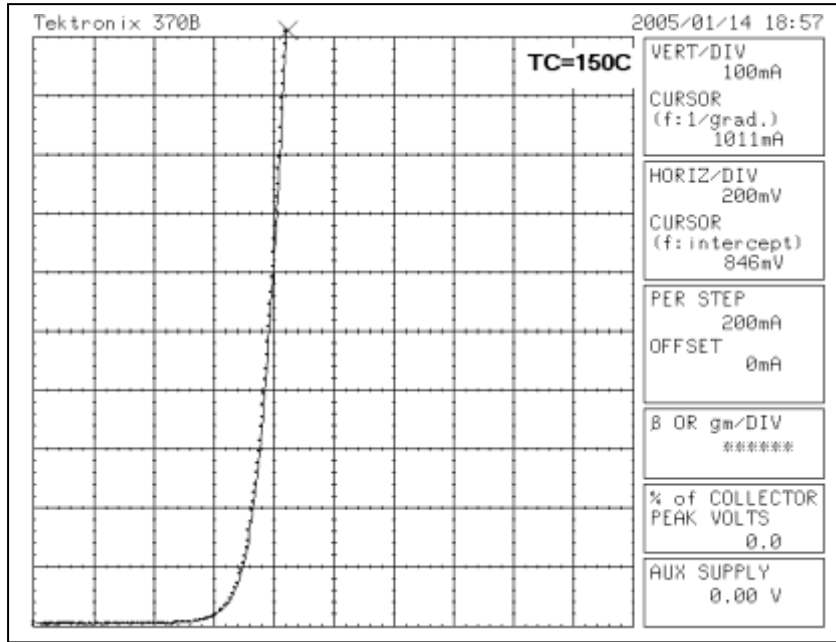


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

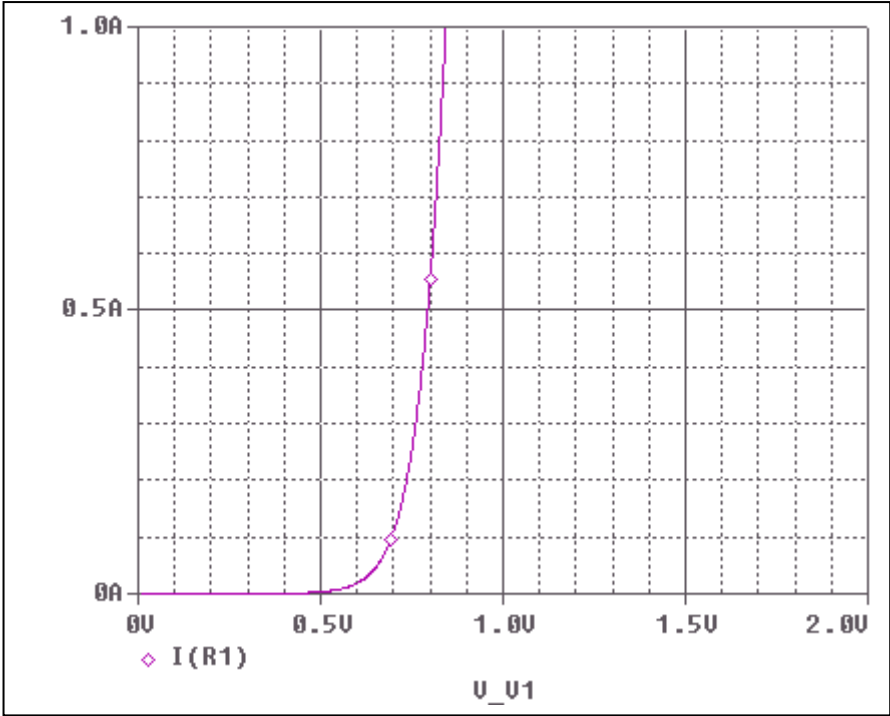
Forward Current Characteristic

Reference

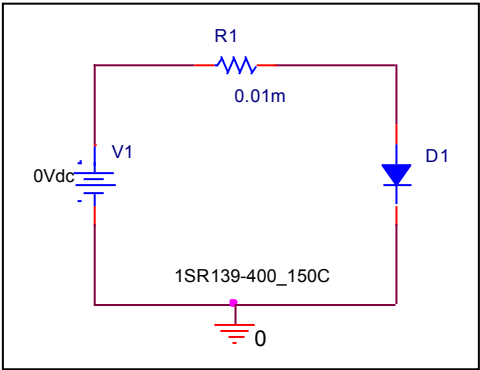


Forward Current Characteristic

Circuit Simulation Result

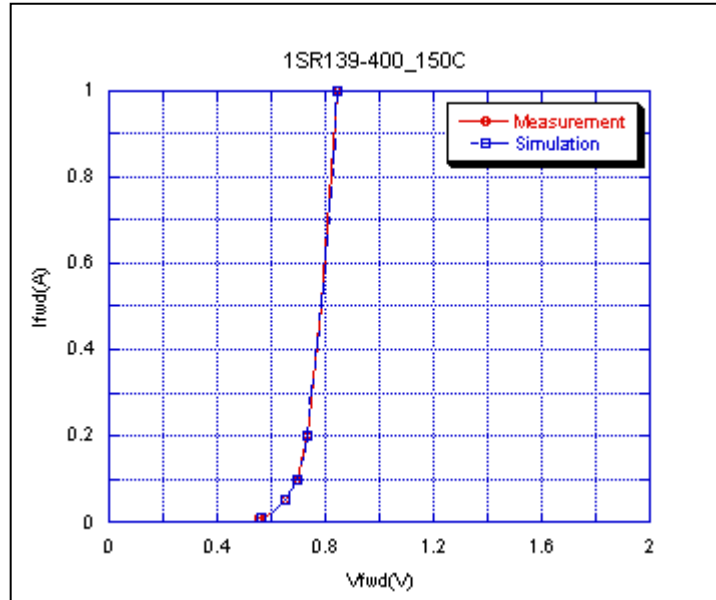


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

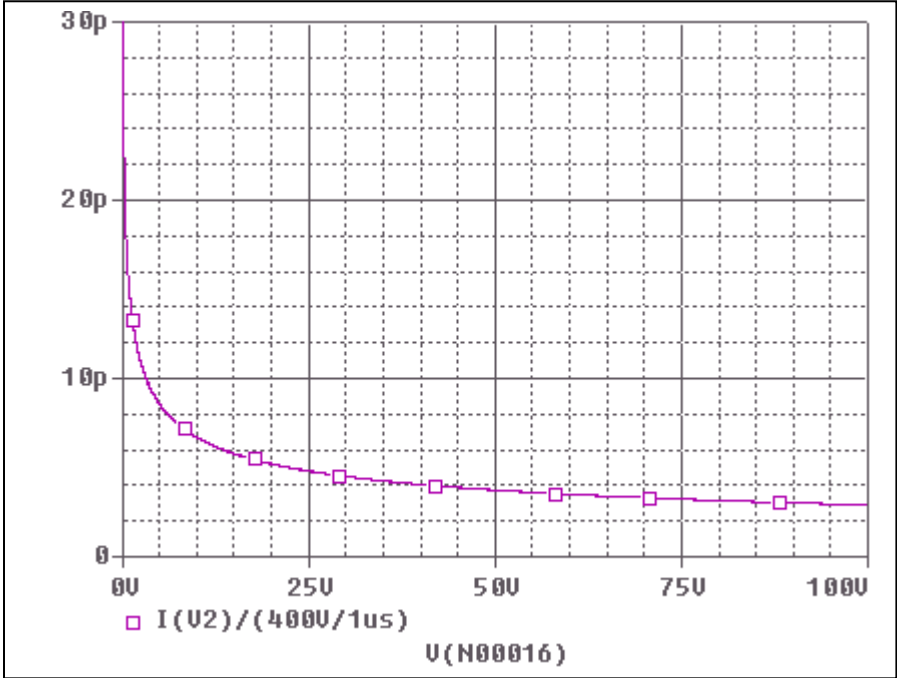


Simulation Result

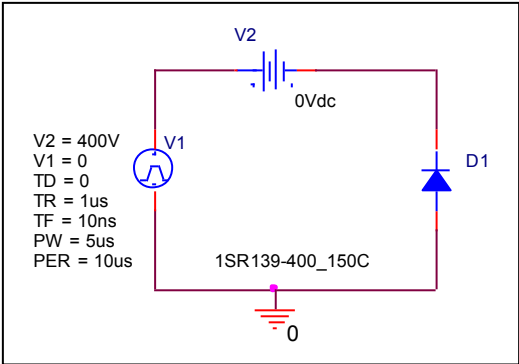
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.01	0.558	0.564	-1.08
0.02	0.600	0.603	-0.50
0.05	0.650	0.655	-0.77
0.1	0.695	0.694	0.14
0.2	0.734	0.735	-0.14
0.5	0.786	0.783	0.38
1	0.846	0.842	0.47

Capacitance Characteristic

Circuit Simulation Result

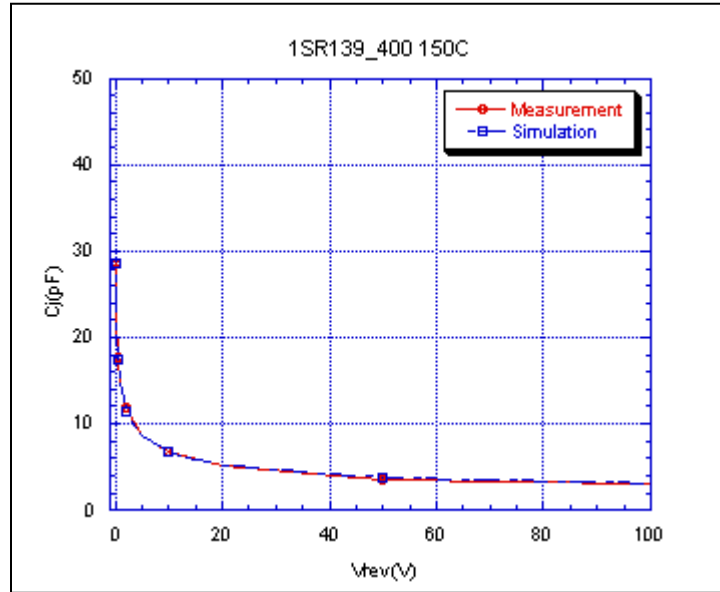


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

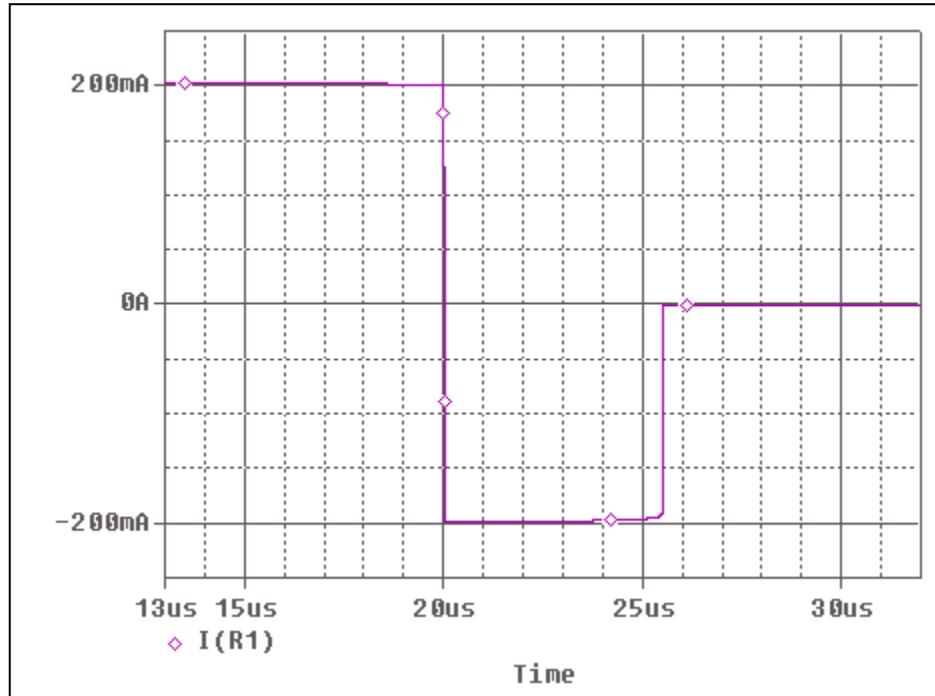


Simulation Result

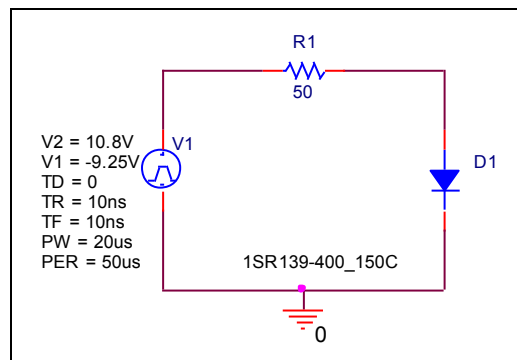
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	28.637	28.637	0.00
0.2	21.867	22.773	-4.14
0.5	17.718	17.392	1.84
1	14.669	15.000	-2.26
2	11.817	11.519	2.52
5	8.695	8.552	1.64
10	6.748	6.680	1.01
20	5.190	5.213	-0.44
50	3.624	3.737	-3.12
100	2.760	2.858	-3.55

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

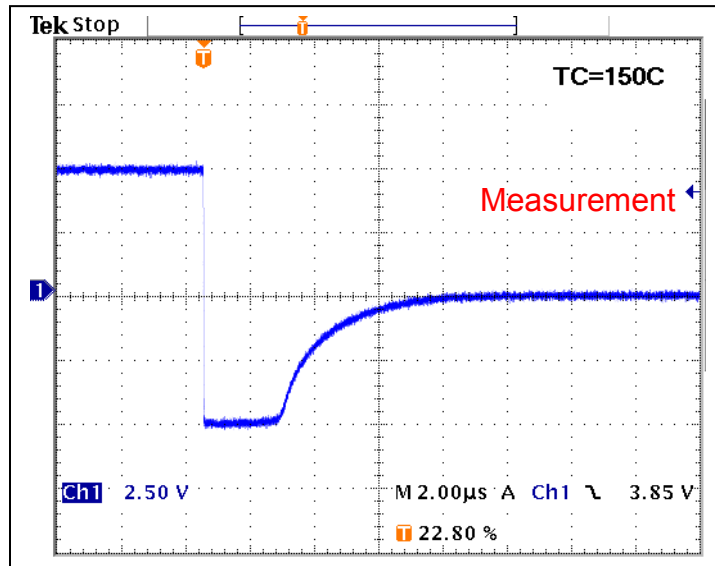


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	5.44	us	5.48	us	0.73

Reverse Recovery Characteristic

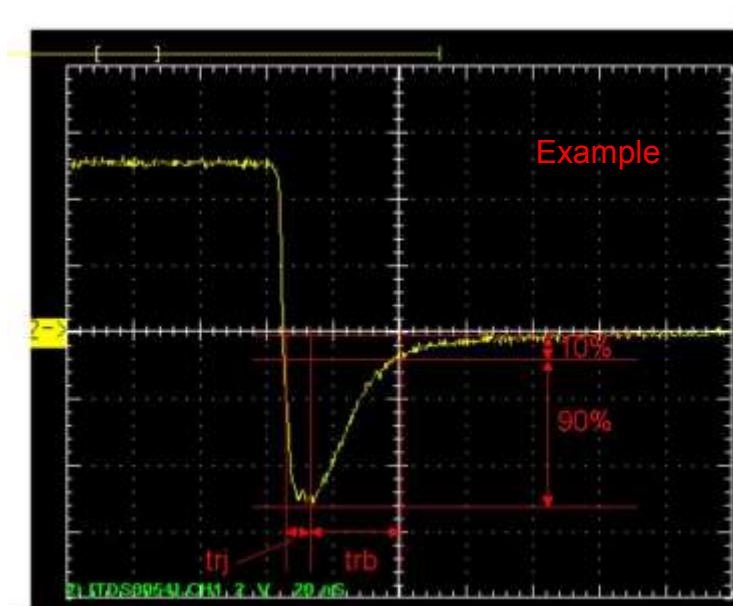
Reference



$T_{rj} = 2.32(\mu s)$

$T_{rb} = 3.12(\mu s)$

Conditions: $I_{fwd} = I_{rev} = 0.2(A)$, $R_I = 50$



Relation between t_{rj} and t_{rb}